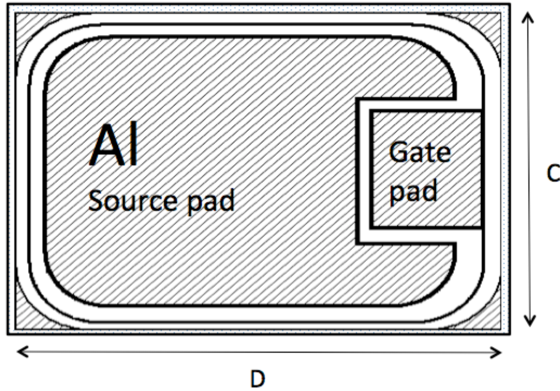
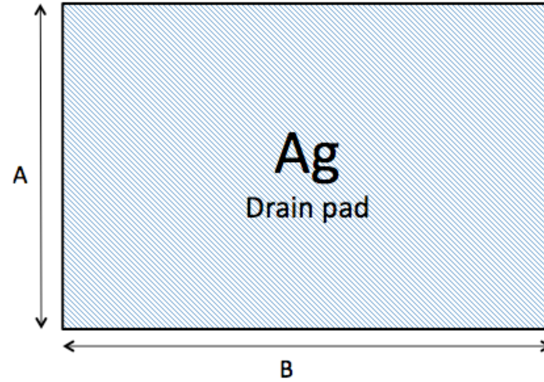
Brückewell

HV MOSFET DIE SPECIFICATION
Product Name: BW-MS7N60C **Version: M**

Chip Features

Front side **Back side**





Chip Size (um)	Thickness (um)	Pad Size-Gate (um)	Pad Size-Source (um)
4,300 * 3,320	350	430 * 550	1200 * 2400
Wafer Size 8 inch	Recommended Wire Bond	Gate Al 6mil * 1	Source Al 10mil * 1
Metalization	TOP: AL	BACK: VA/NI + Ag	

Guranteed PKG Electrical Ratings

T_C = 25°Cunless otherwise noted

Symbol	Parameter	MIN	MAX	Units
BV_{DSS}	Drain-Source Breakdown Voltage (VGS=0V , Id=250uA)	600	-	V
Vth	Gate Threshold Voltage (VDS=VGS , Id=250uA)	2.0	4.0	V
Rdson	Drain-Source On-Resistance (VGS=10V , Id=3.5A)	-	1.2	Ohm
Igss	Gate-Source Leakage Current (VGS=30V, VDS=0V)	-	100	nA
Idss	Drain-Source Leakage Current (VDS=600V,VGS=0V)	-	1.0	uA
Vsd	Drain-Source Forward Voltage Drop (VGS=0V, Is=7.0A)	-	1.5	V

NOTES

1.Detailed device characteristics are available in the device data sheet

2. Drain current limited by maximum junction temperature.